

DERWENT-ACC-NO: 2002-283782
DERWENT-WEEK: 200276
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TITLE: Ceramic substrate for semiconductor or production
inspection apparatus
consists of conductor layer on inside or surface of nitride
ceramic substrate
containing specified compositions of oxygen and silica

INVENTOR: NIWA, T

PATENT-ASSIGNEE: IBIDEN CO LTD[IBIG], NIWA T[NIWAI]

PRIORITY-DATA: 2000JP-0017857 (January 21, 2000)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
PAGES	MAIN-IPC	
US 6475606 B2 000	November 5, 2002 B32B 003/00	N/A
JP 2001206772 012	July 31, 2001 C04B 035/581	N/A
A 012	November 12, 2001 H05B 003/10	N/A
JP 3228924 B2 000	November 22, 2001 B32B 018/00	N/A
US 20010044015 A1		

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE		
US 6475606B2 January 22, 2001	N/A	2001US-0765361
JP2001206772A January 21, 2000	N/A	2000JP-0017857
JP 3228924B2 January 21, 2000	N/A	2000JP-0017857
JP 3228924B2 N/A	Previous Publ.	JP2001206772
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C04B035/581 ;
H01L021/324 ; H01L021/66 ; H05B003/02 ; H05B003/10 ;
H05K001/03

ABSTRACTED-PUB-NO: JP2001206772A
BASIC-ABSTRACT: NOVELTY - The ceramic substrate for semiconductor production-inspection apparatuses, has a conductor layer on the inside or surface of a ceramic substrate of thickness 1-25 μ m and diameter 200 mm or more. The ceramic substrate consists of a nitride ceramic with 0.1-5 weight% of oxygen and 0.1-50 ppm of silica (Si).

USE - Semiconductor production apparatuses like ceramic heater, electrostatic chuck, wafer prober, etching apparatus, chemical vapor phase epitaxy apparatus etc.

ADVANTAGE - Reduction of volume resistivity is suppressed without reducing the temperature rise-temperature fall characteristics. Reduction of heat conductivity and reduction of Young's modulus at high temperature are prevented.

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EQUIVALENT-ABSTRACTS: NOVELTY - The ceramic substrate for semiconductor production-inspection apparatuses, has a conductor layer on the inside or surface of a ceramic substrate of thickness 1-25 μ m and diameter 200 mm or more. The ceramic substrate consists of a nitride ceramic with 0.1-5 weight% of oxygen and 0.1-50 ppm of silica (Si).

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CHOSEN-DRAWING: Dwg. 0/9

TITLE-TERMS:

CERAMIC SUBSTRATE SEMICONDUCTOR PRODUCE INSPECT APPARATUS
CONSIST CONDUCTOR
LAYER SURFACE NITRIDE CERAMIC SUBSTRATE CONTAIN SPECIFIED
COMPOSITION OXYGEN
SILICA

DERWENT-CLASS: L02 L03 P73 U11 V06

CPI-CODES: L02-F03; L04-D;

EPI-CODES: U11-A05B; V06-M06F; V06-U11;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C2002-083413

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